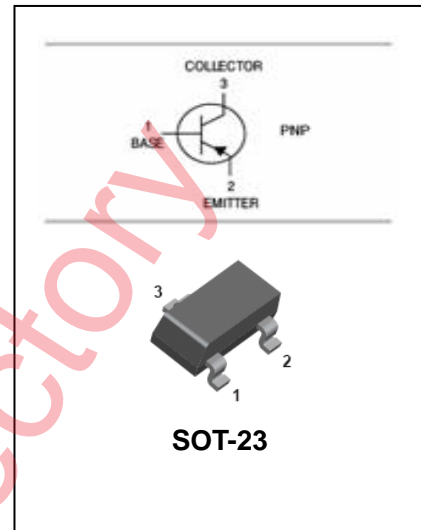


PNP General Purpose Transistor

MMBT3906

FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available (MMBT3904).
- Low Current (Max:-100mA).
- Low Voltage(Max:-40v).



APPLICATIONS

- Ideal for medium power amplification and switching

ORDERING INFORMATION

Type No.	Marking	Package Code
MMBT3906	2A	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-40	V
V _{CEO}	collector-emitter voltage	open base	-	-40	V
V _{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _{BM}	peak base current		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25°C	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note Transistor mounted on an FR4 printed-circuit board.

PNP General Purpose Transistor

MMBT3906

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30 V$	-	-50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 6 V$	-	-50	nA
h_{FE}	DC current gain	$V_{CE} = -1V;$ $I_C = -0.1mA$ $I_C = -1mA$ $I_C = -10mA$ $I_C = -50mA$ $I_C = -100mA$	60 80 100 60 30	- - 300 - -	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10mA; I_B = 1mA$	-	-200	mV
		$I_C = -50mA; I_B = -5mA$	-	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10mA; I_B = -1mA$	-	-850	mV
		$I_C = -50mA; I_B = -5mA$	-	-950	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -5 V;$ $f = 1 MHz$	-	4.5	pF
C_e	emitter capacitance	$I_C = I_c = 0; V_{EB} = -500 mV;$ $f = 1 MHz$	-	10	pF
f_T	transition frequency	$I_C = -10mA; V_{CE} = -20 V;$ $f = 100MHz$	250	-	MHz
NF	noise figure	$I_C = -100\mu A; V_{CE} = -5V;$ $R_S = 1 k\Omega; f = 10Hz to 15.7 kHz$	-	4	dB
Switching times (between 10% and 90% levels);					
t_{on}	Turn-on time	$I_{Con} = -10mA; I_{Bon} = -1mA;$ $I_{Boff} = -1mA$	-	65	ns
t_d	delay time		-	35	ns
t_r	rise time		-	35	ns
t_{off}	turn-off time		-	300	ns
t_s	storage time		-	225	ns
t_f	fall time		-	75	ns

Note Pulse test: $t_p \leq 300 ms; d \leq 0.02.$

PNP General Purpose Transistor

MMBT3906

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

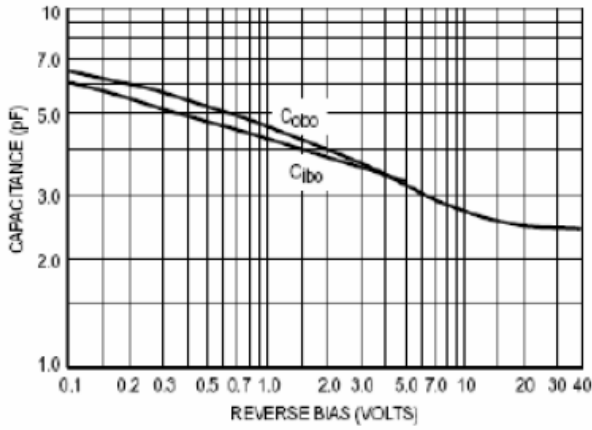


Figure 1 Capacitance

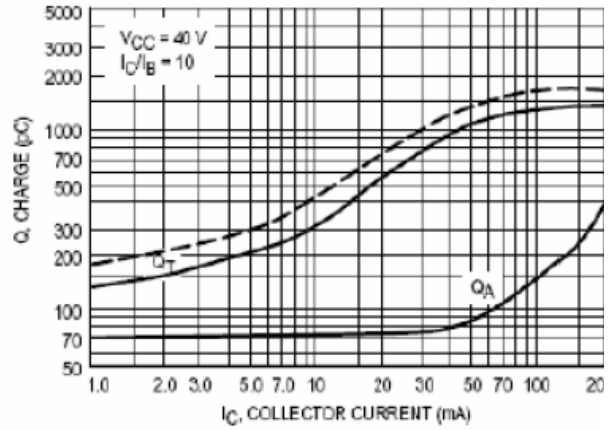


Figure 2 Charge Data

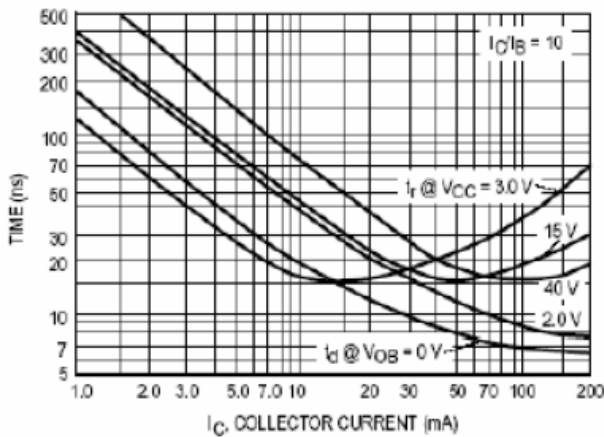


Figure 3 Turn-On Time

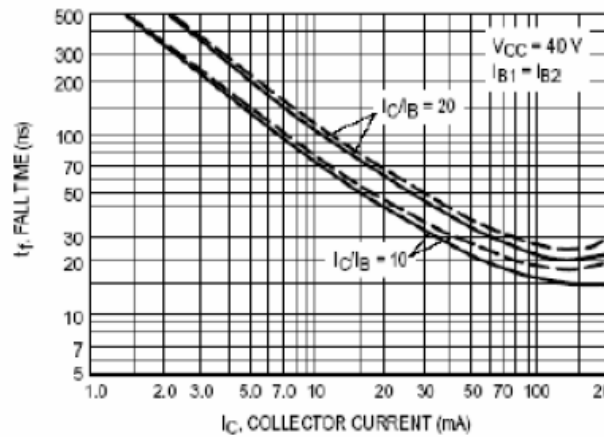


Figure 4 Fall Time

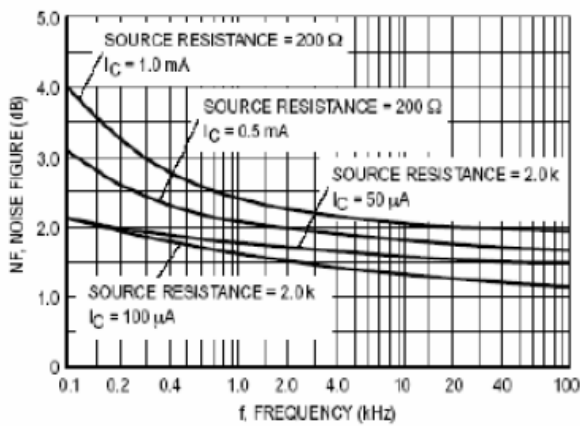


Figure 5

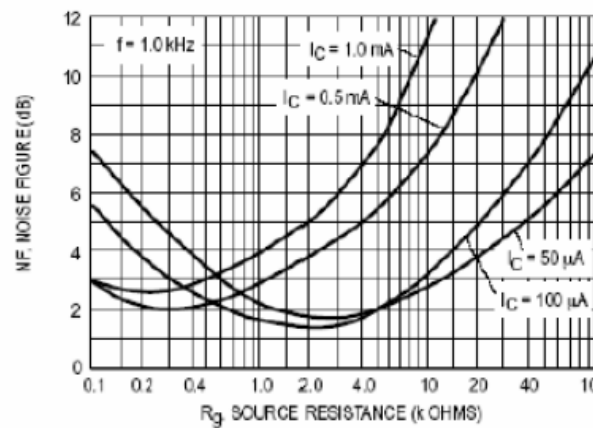


Figure 6

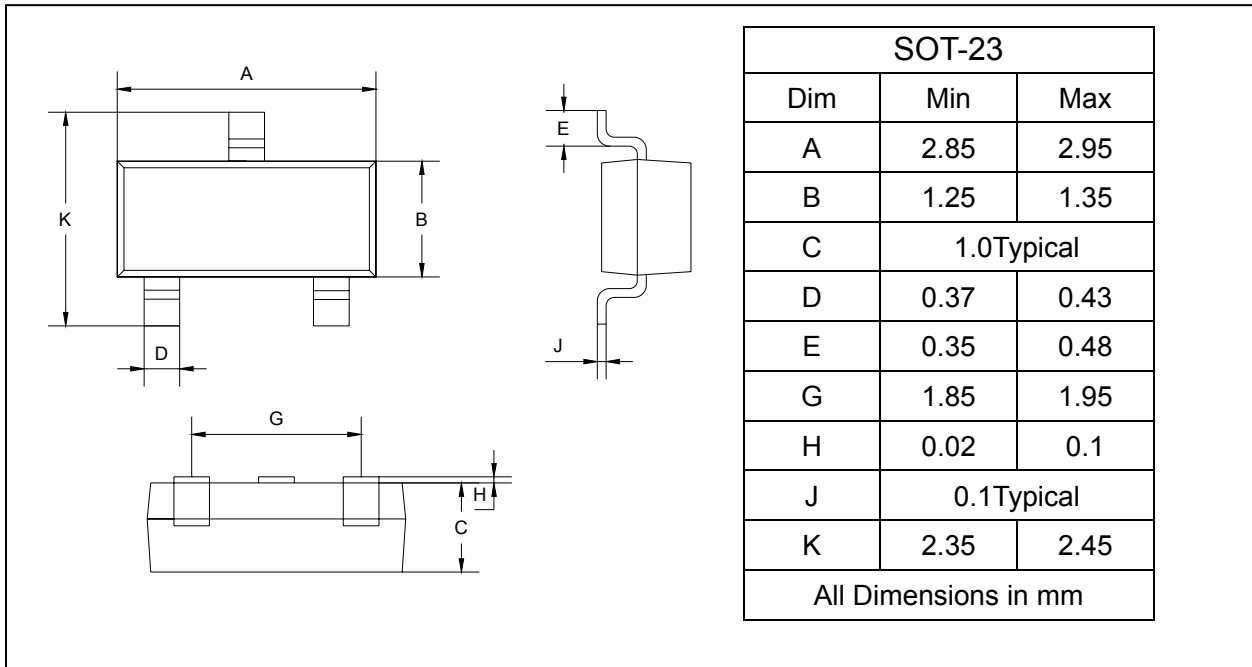
PNP General Purpose Transistor

MMBT3906

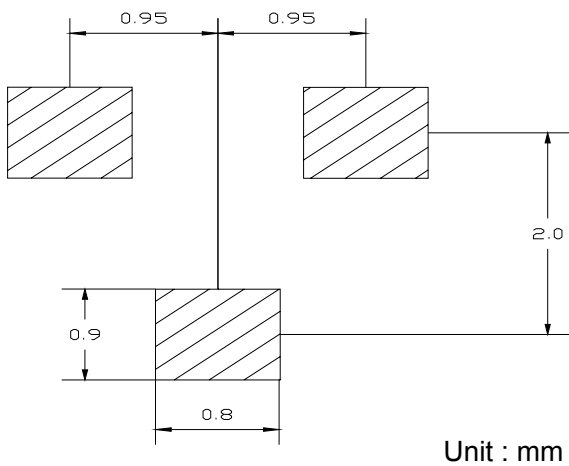
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMBT3906	SOT-23	3000/Tape&Reel